

RJH60D1DPE

Silicon N Channel IGBT Application: Inverter

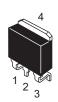
REJ03G1840-0100 Rev.1.00 Oct 14, 2009

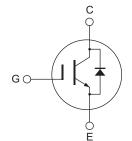
Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

Outline

RENESAS Package code: PRSS0004AE-B (Package name: LDPAK (S)-(1))





- 1. Gate
- 2. Collector
- 3. Emitter
- 4. Collecotor

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

	Item	Symbol	Ratings	Unit
Collector to emitter voltage / diode reverse voltage		V _{CES} / V _R	600	V
Gate to emitter voltage		V_{GES}	±30	V
Collector current	Tc = 25°C	Ic	16	Α
	Tc = 100°C	Ic	8	Α
Collector peak current	·	ic(peak) Note1	32	Α
Collector to emitter dio	de forward current	i _{DF}	8	Α
Collector to Emitter diode forward peak current		i _{DF} (peak) Note1	32	Α
Collector dissipation		P _C Note2	70	W
Junction to case thermal impedance		θj-c ^{Note2}	1.79	°C/W
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C
Nister 4 DW +40		•		

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

RJH60D1DPE Preliminary

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

 $di_F/dt = 100 A/\mu s$

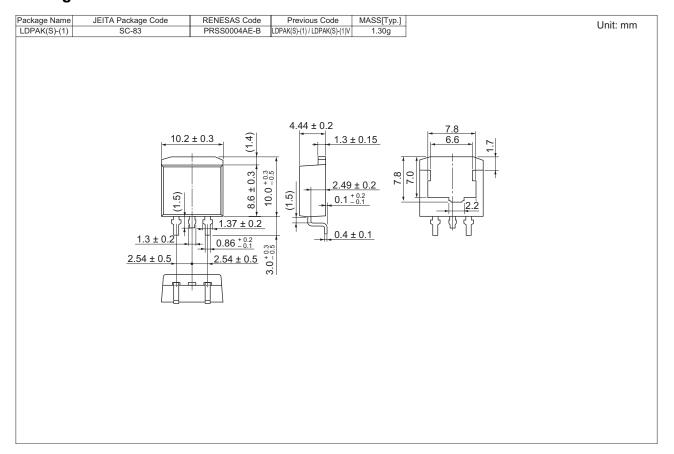
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current	I _{CES} / I _R	_	_	100	μΑ	V _{CE} = 600 V, V _{GE} = 0
/ Diode reverse current						
Gate to emitter leak current	I_{GES}	_	_	±1	μΑ	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{\text{GE(off)}}$	4.0	_	6.0	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$		1.8	2.2	V	I _C = 8 A, V _{GE} = 15 V ^{Note3}
	$V_{CE(sat)}$	_	2.3		V	$I_C = 16 \text{ A}, V_{GE} = 15 \text{ V}^{\text{Note3}}$
Input capacitance	Cies	-	290	_	pF	V _{CE} = 25 V
Output capacitance	Coes	_	25	_	pF	$V_{GE} = 0$
Reveres transfer capacitance	Cres	_	7.5	_	pF	f = 1 MHz
Total gate charge	Qg	_	12.0	_	nC	V _{GE} = 15 V
Gate to emitter charge	Qge	_	2.0	_	nC	V _{CE} = 300 V
Gate to collector charge	Qgc	_	6.0	_	nC	I _C = 8 A
Switching time	t _{d(on)}	_	25	_	ns	I _C = 8 A
	t _r	_	35	_	ns	$R_L = 37.5 \Omega$
	t _{d(off)}	_	40	_	ns	V _{GE} = 15 V
	t _f	_	100	_	ns	$Rg = 5 \Omega$
FRD forward voltage	V _F	_	1.8	2.3	V	I _F = 8 A ^{Note3}
FRD reverse recovery time	t _{rr}	_	100	_	ns	I _F = 8 A

Notes: 3. Pulse test.

^{4.} Under development. –The specification potentially be changed without notice.

RJH60D1DPE Preliminary

Package Dimension



Ordering Information

Part No.	Quantity	Shipping Container
RJH60D1DPE-00-J3	1000 pcs	Taping

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect to the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510